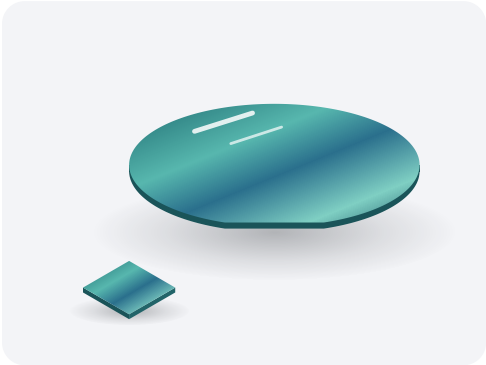
SERIES S22 · NITRIDE

Silicon nitride coated wafers



LPCVD stoichiometric or low-stress silicon nitride, and PECVD nitride for lower-temperature work. Used for membranes, photonic waveguides, KOH-etch masks and passivation layers.

- LPCVD Si_3N_4: refractive index ≈ 2.0 at 633 nm
- LPCVD films on both sides; PECVD on the front side
- Substrate: P-type ⟨100⟩ silicon, 1 – 10 Ω·cm
- Diced chips available (series S23)

CONFIGURATIONS

Ref. No.	Film	Process	Film thickness	Wafer	Price
S2201	Stoichiometric Si_3N_4	LPCVD	50 nm	2"	On request
S2202	Stoichiometric Si_3N_4	LPCVD	50 nm	4"	On request
S2203	Stoichiometric Si_3N_4	LPCVD	50 nm	6"	On request
S2204	Stoichiometric Si_3N_4	LPCVD	100 nm	2"	On request
S2205	Stoichiometric Si_3N_4	LPCVD	100 nm	4"	On request
S2206	Stoichiometric Si_3N_4	LPCVD	100 nm	6"	On request
S2207	Stoichiometric Si_3N_4	LPCVD	200 nm	2"	On request
S2208	Stoichiometric Si_3N_4	LPCVD	200 nm	4"	On request
S2209	Stoichiometric Si_3N_4	LPCVD	200 nm	6"	On request
S2210	Stoichiometric Si_3N_4	LPCVD	300 nm	2"	On request
S2211	Stoichiometric Si_3N_4	LPCVD	300 nm	4"	On request
S2212	Stoichiometric Si_3N_4	LPCVD	300 nm	6"	On request
S2213	Low-stress SiN_x (< 250 MPa)	LPCVD	100 nm	2"	On request
S2214	Low-stress SiN_x (< 250 MPa)	LPCVD	100 nm	4"	On request
S2215	Low-stress SiN_x (< 250 MPa)	LPCVD	100 nm	6"	On request
S2216	Low-stress SiN_x (< 250 MPa)	LPCVD	200 nm	2"	On request
S2217	Low-stress SiN_x (< 250 MPa)	LPCVD	200 nm	4"	On request
S2218	Low-stress SiN_x (< 250 MPa)	LPCVD	200 nm	6"	On request
S2219	Low-stress SiN_x (< 250 MPa)	LPCVD	500 nm	2"	On request
S2220	Low-stress SiN_x (< 250 MPa)	LPCVD	500 nm	4"	On request
S2221	Low-stress SiN_x (< 250 MPa)	LPCVD	500 nm	6"	On request
S2222	Low-stress SiN_x (< 250 MPa)	LPCVD	1000 nm	2"	On request
S2223	Low-stress SiN_x (< 250 MPa)	LPCVD	1000 nm	4"	On request
S2224	Low-stress SiN_x (< 250 MPa)	LPCVD	1000 nm	6"	On request
S2225	SiN_x (front side)	PECVD	100 nm	2"	On request
S2226	SiN_x (front side)	PECVD	100 nm	4"	On request
S2227	SiN_x (front side)	PECVD	100 nm	6"	On request

Ref. No.	Film	Process	Film thickness	Wafer	Price
S2228	SiN_x (front side)	PECVD	200 nm	2"	On request
S2229	SiN_x (front side)	PECVD	200 nm	4"	On request
S2230	SiN_x (front side)	PECVD	200 nm	6"	On request
S2231	SiN_x (front side)	PECVD	500 nm	2"	On request
S2232	SiN_x (front side)	PECVD	500 nm	4"	On request
S2233	SiN_x (front side)	PECVD	500 nm	6"	On request
S2234	Si_3N_4 on SiO_2 stack	LPCVD + thermal	100 nm / 1 µm	2"	On request
S2235	Si_3N_4 on SiO_2 stack	LPCVD + thermal	100 nm / 1 µm	4"	On request
S2236	Si_3N_4 on SiO_2 stack	LPCVD + thermal	100 nm / 1 µm	6"	On request

Specifications are typical values; every lot ships with a Certificate of Conformance, and measured data are available on request. Prices on request.